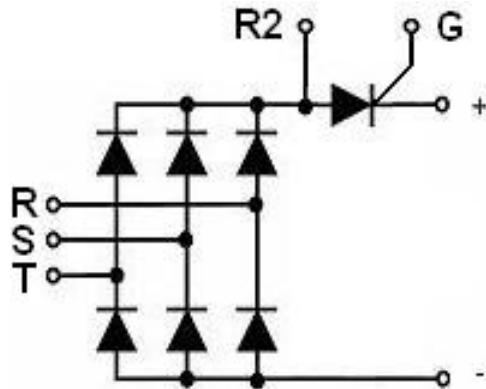


## PRODUCT FEATURES

- Electrically Isolated by DBC Ceramic
- High Surge Current Capability
- Low Inductance Package

## APPLICATIONS

- DC Motor Control and Drives
- Battery Charges ,Heater controls,Light dimmers
- Static switches



## **MAXIMUM VOLTAGE RATINGS**

 $T_c = 25^\circ\text{C}$  unless otherwise specified

Module Type	$V_{RRM}/V_{DRM}$	$V_{RSM}$	Unit
MMK150T160UX6J	1600	1700	V

## **ABSOLUTE MAXIMUM RATINGS (Thyristor)**

Symbol	Parameter/Test Conditions		Values	Unit
$I_{T(AV)}$	Average On-State Current	Single phase, half wave, 180° conduction, $T_c = 80^\circ\text{C}$	150	A
$I_{T(RMS)}$	R.M.S. On-State Current		225	
$I_{TSM}$	Non-Repetitive Surge On-State Current	1/2 cycle, 50/60HZ, peak value, $T_c = 45^\circ\text{C}$		3600/3800
$I^2t$	$I^2t$ (For Fusing)	1/2 cycle, 50/60HZ, peak value, $T_c = 45^\circ\text{C}$		64.8/59.8 $\text{KA}^2\text{s}$
$T_J$	Junction Temperature(Thyristor)			-40 to +125 $^\circ\text{C}$

## **ABSOLUTE MAXIMUM RATINGS (Diode)**

Symbol	Parameter/Test Conditions		Values	Unit
$I_{F(AV)}$	Average Forward Current	Single phase, half wave, 180° conduction, $T_c = 95^\circ\text{C}$	150	A
$I_{F(RMS)}$	R.M.S. Forward Current		225	
$I_{FSM}$	Non-Repetitive Surge Forward Current	1/2 cycle, 50/60HZ, peak value, $T_c = 45^\circ\text{C}$		1700/1800
$I^2t$	For Fusing	1/2 cycle, 50/60HZ, peak value, $T_c = 45^\circ\text{C}$		14.4/13.4 $\text{KA}^2\text{s}$
$T_J$	Junction Temperature(Diode)			-40 to +150 $^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS (Thyristor)** $T_C = 25^\circ\text{C}$  unless otherwise specified

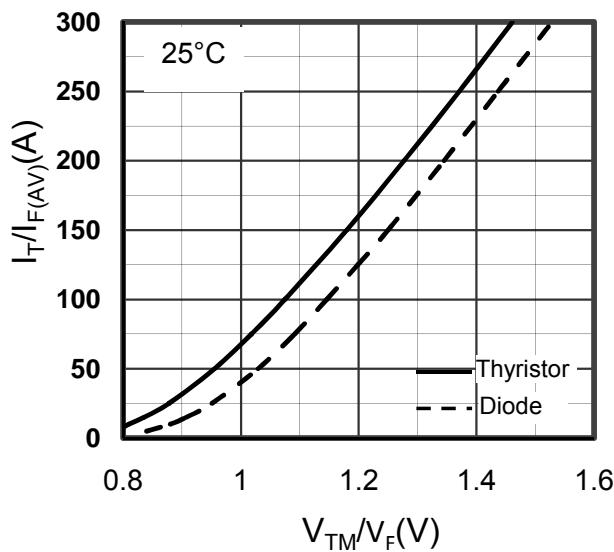
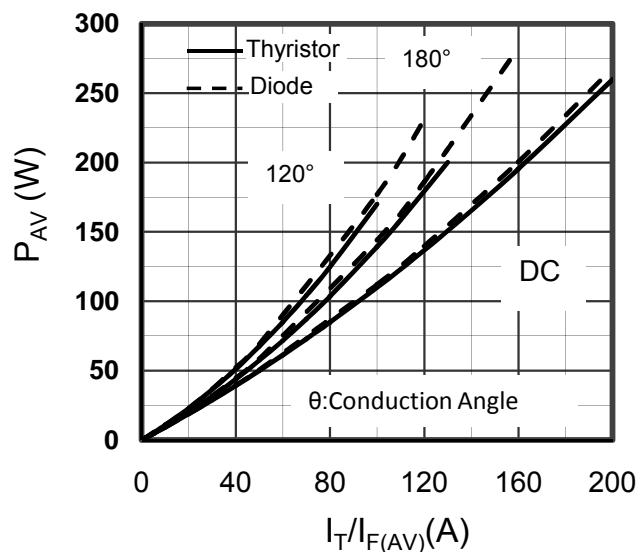
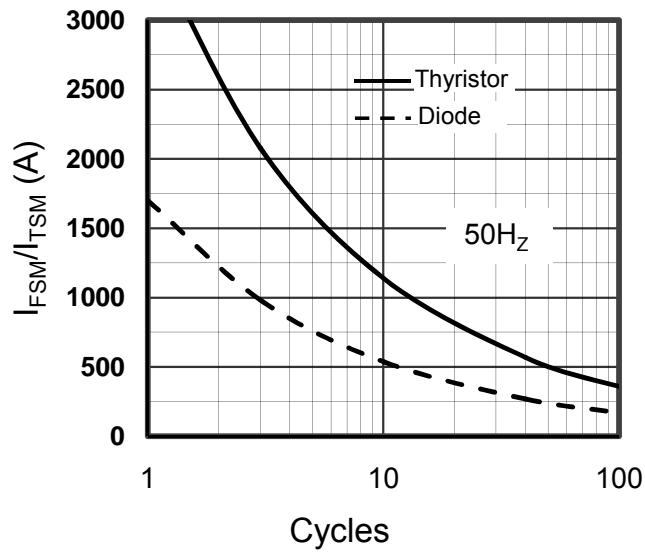
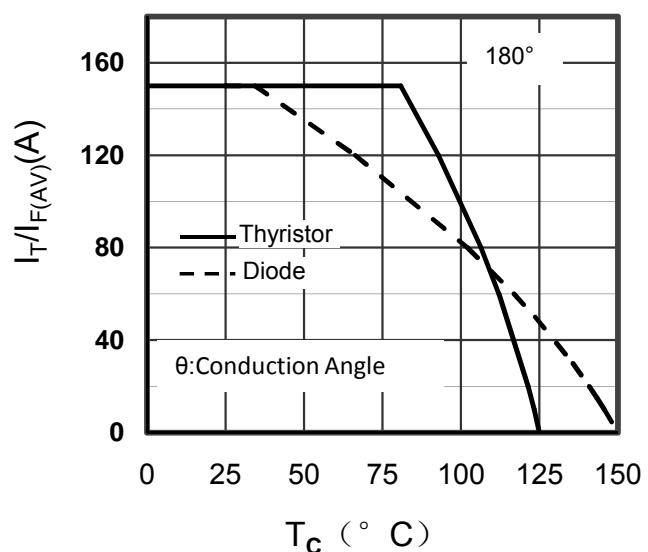
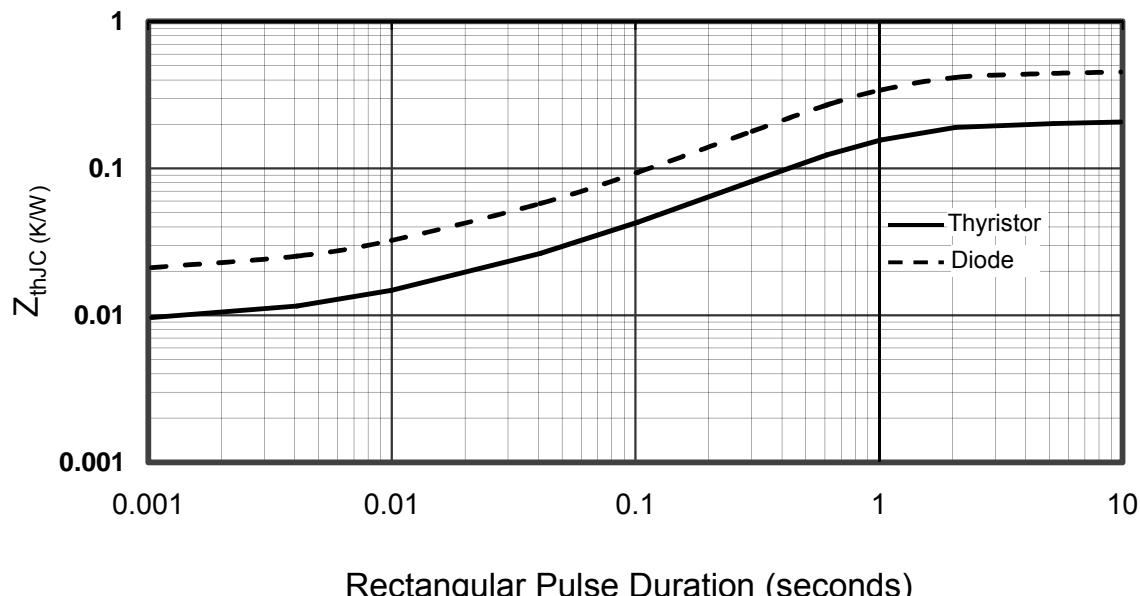
Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit	
$I_{DRM}$	Maximum Peak Off-State Current $V_D = V_{DRM}, T_J = 125^\circ\text{C}$			25	mA	
$I_{RRM}$	Maximum Peak Reverse Current $V_R = V_{RRM}, T_J = 125^\circ\text{C}$			25		
$V_{TM}$	Maximum on-state voltage drop $I_{TM}=150\text{A}, t_d=10\text{ ms, half sine}$			1.18	V	
$V_{TO}$	For power-loss calculations only	$T_J = 125^\circ\text{C}$		0.9	V	
$r_T$				2.0	$\text{m}\Omega$	
$V_{GT}$	Max. required DC gate voltage to trigger	$V_A=6\text{V}, R_A=1\Omega, T_J = -40^\circ\text{C}$		4.0	V	
		$V_A=6\text{V}, R_A=1\Omega$		0.8		
		$V_A=6\text{V}, R_A=1\Omega, T_J = 125^\circ\text{C}$		1.7		
$I_{GT}$	Max. required DC gate current to trigger	$V_A=6\text{V}, R_A=1\Omega, T_J = -40^\circ\text{C}$		270	mA	
		$V_A=6\text{V}, R_A=1\Omega$		65		
		$V_A=6\text{V}, R_A=1\Omega, T_J = 125^\circ\text{C}$		80		
$V_{GD}$	Max. required DC gate voltage not to trigger, $V_D = V_{DRM}, T_J = 125^\circ\text{C}$			0.25	V	
$I_{GD}$	Max. required DC gate current not to trigger, $V_D = V_{DRM}, T_J = 125^\circ\text{C}$			6	mA	
$I_H$	Maximum holding current			200	400	mA
$I_L$	Maximum latching current			250	500	mA
$P_{GM}$	Maximum peak gate power			12	W	
$P_{G(AV)}$	Maximum average gate power			3.0		
$I_{GM}$	Maximum peak gate current			3.0	A	
$-V_{GM}$	Maximum peak negative gate voltage			10	V	
$dv/dt$	Critical Rate of Rise of Off-State Voltage, $T_J=125^\circ\text{C}$ , exponential to 67% rated $V_{DRM}$			1000	$\text{V}/\mu\text{s}$	
$di/dt$	Max.Rate of Rise of Turned-on Current, $T_J = 125^\circ\text{C}, I_{TM}=500\text{A}$ , rated $V_{DRM}$			150	$\text{A}/\mu\text{s}$	

**ELECTRICAL CHARACTERISTICS (Diode)**

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = V_{RRM}$		0.5	mA
		$V_R = V_{RRM}, T_J = 125^\circ\text{C}$		10	
$V_F$	Forward Voltage Drop $I_F=150\text{A}$			1.25	V
$V_{TO}$	For power-loss calculations only , $T_J = 125^\circ\text{C}$			0.9	V
				2.2	$\text{m}\Omega$

**MODULE CHARACTERISTICS** $T_C = 25^\circ\text{C}$  unless otherwise specified

$T_{STG}$	Storage Temperature Range	-40 to +125	°C
$V_{ISO}$	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	V
<b>Torque</b>	to heatsink	Recommended (M6)	N.m
<b>Torque</b>	to terminal	Recommended (M6)	N.m
$R_{th(J-C)}$	Junction-to-Case Thermal Resistance(Per Thyristor/Per Diode)	0.18/0.45	K /W
<b>Weight</b>		330	g


**Figure1. Forward Voltage Drop vs Forward Current**

**Figure2. Power dissipation vs.  $I_T/I_{F(AV)}$** 

**Figure3. Diode and SCR Max Non-Repetitive Surge**

**Figure4. Diode  $I_{F(AV)}$  and SCR  $I_{T(AV)}$ vs. $T_C$** 

**Figure5. Transient Thermal Impedance of Diode and SCR**

Instantaneous Gate Voltage (V)

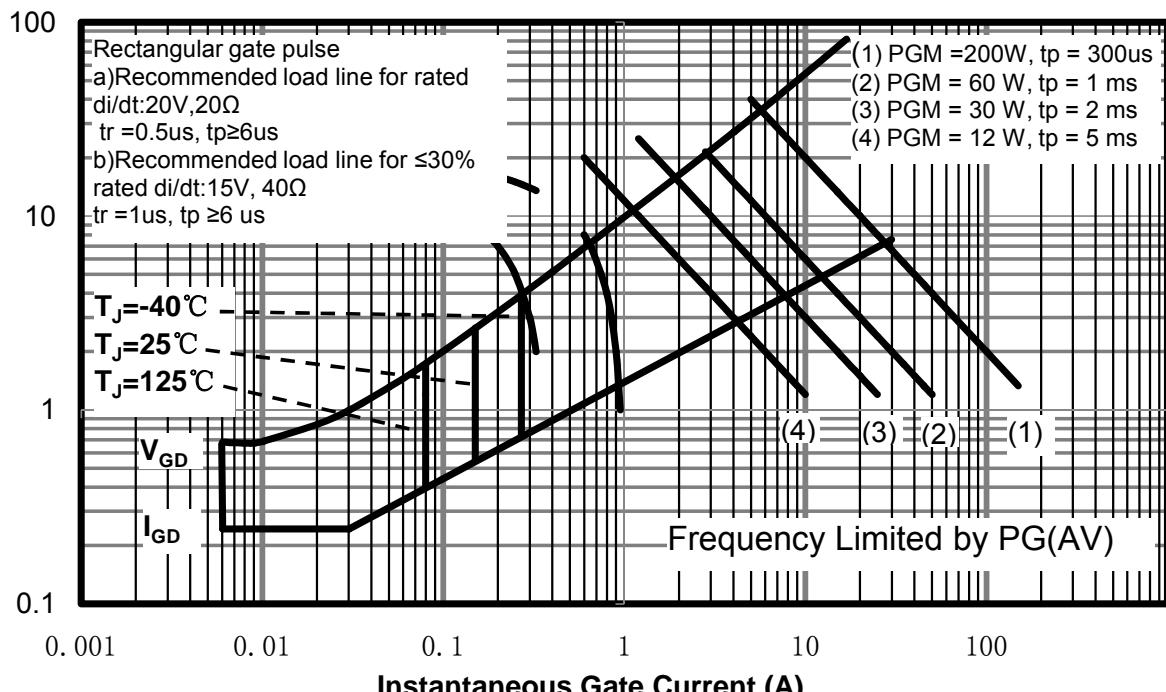
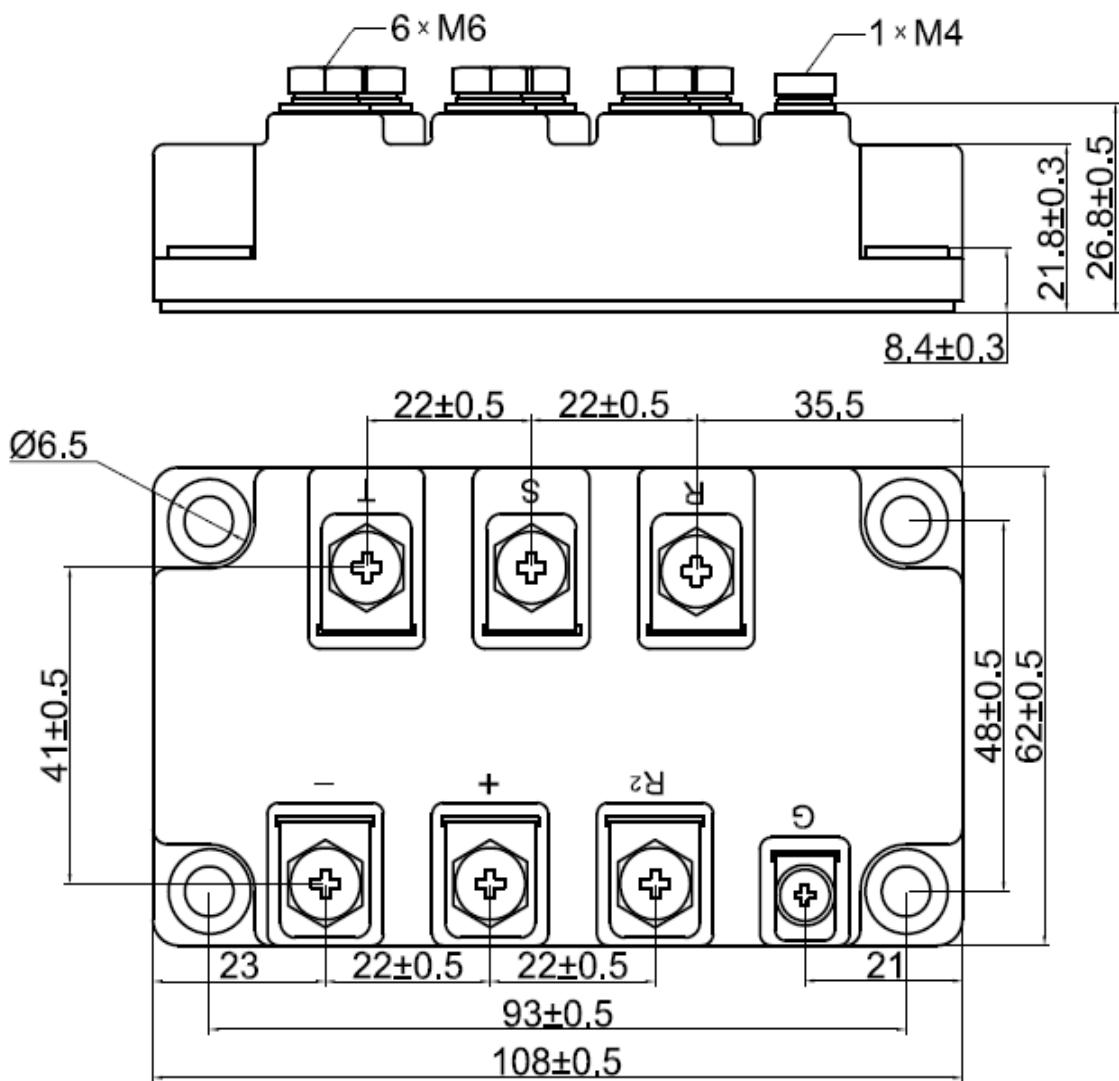


Figure 6. SCR Gate Characteristics



Dimensions in Millimeters

Figure 7. Package Outline